

In the Claims:

1. (Currently Amended) An integrated circuit comprising:
 - a first substantially planar dielectric layer;
 - first conductive lines on a first level, said first conductive lines having a selected width and spaced apart a distance substantially equal to said selected width and located in said first dielectric layer;
 - a second substantially planar dielectric layer formed over said first dielectric layer;
 - second conductive lines on a second level, said second conductive lines having a selected width and spaced apart a distance substantially equal to said selected width and located in said second dielectric layer; and
 - at least one of said first conductive lines or said second conductive lines comprising a non-rectangular shaped cross-section.
2. (Currently Amended) The integrated circuit of claim 1 wherein both said first conductive lines ~~lines~~ and said second conductive lines have a non-rectangular cross-section.
3. (Currently Amended) ~~The integrated circuit of claim 2 wherein said cross-section of said first and second conductive lines is triangular.~~ An integrated circuit comprising:
 - a first substantially planar dielectric layer;
 - first conductive lines on a first level having a triangular cross-section and located in said first dielectric layer;
 - a second substantially planar dielectric layer formed over said first dielectric layer;
 - second conductive lines on a second level having a triangular cross-section and located in said second dielectric layer.

4. (Previously Presented) The integrated circuit of claim 2 wherein said cross-section of said first and second conductive lines is trapezoidal.
5. (Previously Presented) The integrated circuit of claim 3 wherein the uppermost portion of said conductive lines on said first level is below the lowermost portion of said conductive lines on said second level.
6. (Currently Amended) The integrated circuit of claim 3 ~~claim 2~~ wherein the uppermost portion of said conductive lines in said first level is co-planar with the lowermost portion of said conductive lines in said second level.
7. (Previously Presented) The integrated circuit of claim 1 wherein at least one sidewall of said non-rectangular shaped cross-section is non-vertical.
8. (Previously Presented) The integrated circuit of claim 2 wherein at least one sidewall of said non-rectangular shaped cross-section is non-vertical.
9. (Currently Amended) The integrated circuit of claim 3 ~~claim 1~~ wherein the conductive lines comprise a conductive material selected from a group consisting of aluminum, copper or alloys thereof.
10. (Currently Amended) ~~The integrated circuit of claim 1 wherein the pitch between adjacent first conductive lines and between adjacent second conductive lines is less than 2F.~~ An integrated circuit comprising:

a first substantially planar dielectric layer;

first conductive lines on a first level and located in said first dielectric layer;
a second substantially planar dielectric layer formed over said first dielectric layer;
second conductive lines on a second level and located in said second dielectric layer; and
at least one of said first conductive lines or said second conductive lines comprising a non-
rectangular shaped cross-section; and wherein the pitch between adjacent first conductive lines and
between adjacent second conductive lines is less than $2F$.

11. (Currently Amended) An integrated circuit comprising:

first conductive parallel lines on one level separated by a selected pitch, said first conductive parallel lines having a selected width and spaced apart a distance substantially equal to said selected width;

second conductive parallel lines electrically isolated from said first conductive parallel lines located on another level separated by said selected pitch and having a non-rectangular shaped cross-section such that said first and second said conductive parallel lines may be arranged to reduce capacitance between said first and second conductive parallel lines at said selected pitch, said second conductive parallel lines having a selected width and spaced apart a distance substantially equal to said selected width.

12. (Previously Presented) The integrated circuit of claim 11 wherein said first conductive parallel lines have a rectangular cross-section.

13. (Previously Presented) The integrated circuit of claim 11 wherein said first conductive parallel lines have a non-rectangular cross-section.

14. (Previously Presented) The integrated circuit of claim 13 wherein said cross-sectional shape of said first and second conductive parallel lines is triangular shape.

15. (Currently Amended) ~~The integrated circuit of claim 14 wherein said one level is a lower level and said another level is an upper level.~~ An integrated circuit comprising:

first conductive parallel lines having a triangular cross-section on a lower level separated by a selected pitch;

second conductive parallel lines having a triangular cross-section on an upper level separated by said selected pitch such that said first and second said conductive parallel lines may be arranged to reduce capacitance between said first and second conductive parallel lines at said selected pitch and wherein the vertex of said triangular cross-sectional conductive parallel lines on said lower level points toward said second level and wherein the vertex of said triangular cross-sectional conductive parallel lines on said upper level points toward said lower level.

16. (Previously Presented) The integrated circuit of claim 15 wherein the vertexes of said conductive parallel lines on said lower level is co-planar with the vertexes of said conductive parallel lines on said upper level.

17. (Previously Presented) The integrated circuit of claim 15 wherein the vertexes of said conductive parallel lines on said upper level are spaced a selected distance vertically from the vertexes of said conductive parallel lines on said lower level.

18. (Previously Presented) The integrated circuit of claim 11 wherein said conductive parallel lines on said another level have first and second sidewalls and wherein at least one of said first and second sidewalls is non-vertical.
19. (Previously Presented) The integrated circuit of claim 13 wherein said cross-section shape of said first and second conductive parallel lines is trapezoidal shaped.
20. (Currently Amended) The integrated circuit of claim 11 ~~claim 2~~ wherein said one level is a lower level and said another level is an upper level.
21. (Currently Amended) The integrated circuit of claim 11 ~~claim 2~~ wherein said one level is an upper level and said another level is a lower level.
22. (Previously Presented) The integrated circuit of claim 18 wherein the first and second sidewalls are completely non-vertical.
23. (Currently Amended) ~~The integrated circuit of claim 11 wherein the selected pitch is less than~~
2F. An integrated circuit comprising:
first conductive parallel lines on one level separated by a selected pitch of less than 2F;
second conductive parallel lines on another level separated by said selected pitch and having a
non-rectangular shaped cross-section such that said first and second said conductive parallel lines may
be arranged to reduce capacitance between said first and second conductive parallel lines at said
selected pitch.

24. (Currently Amended) The integrated circuit of claim 23 ~~claim 11~~ wherein the selected pitch is about 1.5F.
25. (New) The integrated circuit of claim 3 wherein both said first conductive lines and said second conductive lines have a non-rectangular cross-section.
26. (New) The integrated circuit of claim 25 wherein said cross-section of said first and second conductive lines is triangular.
27. (New) The integrated circuit of claim 3 wherein the uppermost portion of said conductive lines on said first level is below the lowermost portion of said conductive lines on said second level.
28. (New) The integrated circuit of claim 2 wherein the uppermost portion of said conductive lines in said first level is co-planar with the lowermost portion of said conductive lines in said second level.
29. (New) The integrated circuit of claim 10 wherein the conductive lines comprise a conductive material selected from a group consisting of aluminum, copper or alloys thereof.